

REJ03G0636-0200 (Previous ADE-208-1008) Rev.2.00 Aug.10.2005

Application

- Low frequency amplifier
- Complementary pair with 2SC2618

Outline

Absolute Maximum Ratings

			(Ta = 25°C)
Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	-35	V
Collector to emitter voltage	V _{CEO}	-35	V
Emitter to base voltage	V _{EBO}	-4	V
Collector current	Ι _C	-500	mA
Collector power dissipation	Pc	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C



Electrical Characteristics

$(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	V _{(BR)CBO}	-35	_	_	V	$I_{\rm C} = -10 \ \mu A, \ I_{\rm E} = 0$
Collector to emitter breakdown voltage	V _{(BR)CEO}	-35	_	_	V	$I_{C} = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	V _{(BR)EBO}	-4	_		V	$I_E = -10 \ \mu A, \ I_C = 0$
Collector cutoff current	I _{CBO}		_	-0.5	μΑ	$V_{CB} = -20 \text{ V}, I_E = 0$
Collector to emitter saturation voltage	V _{CE(sat)}	—	-0.2	-0.6	V	$I_{\rm C} = -150 \text{ mA}, I_{\rm B} = -15 \text{ mA}$
DC current transfer ratio	h _{FE} * ¹	100		320		$V_{CE} = -3 V$, $I_C = -10 mA$
	h _{FE}	10	—	_		$V_{CE} = -3 V$, $I_C = -500 mA$
						(Pulse test)
Base to emitter voltage	V _{BE}	_	-0.64	_	V	$V_{CE} = -3 V, I_C = -10 mA$

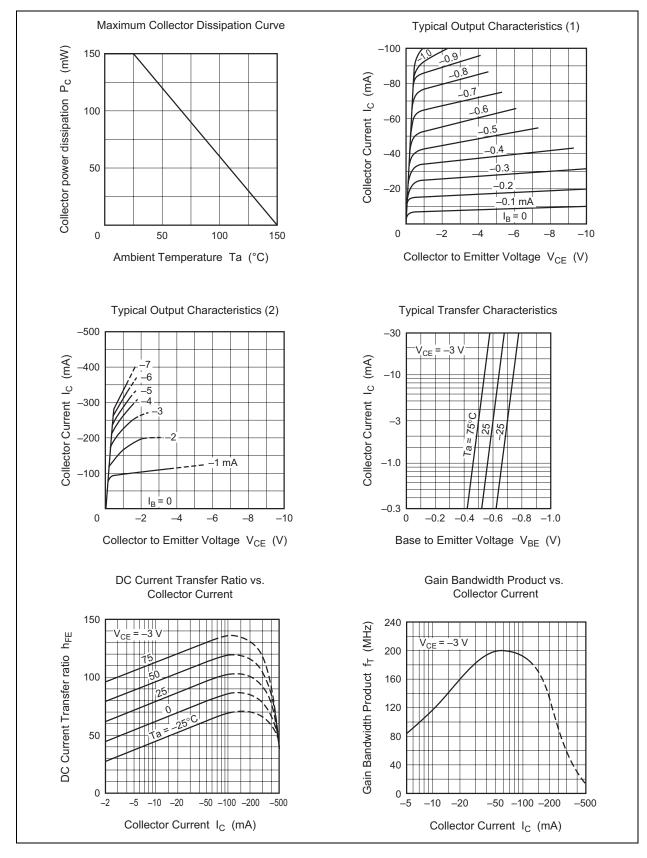
Note: 1. The 2SA1121 is grouped by h_{FE} as follows.

Grade	С	D	
Mark	SC	SD	
h _{FE}	100 to 200	160 to 320	

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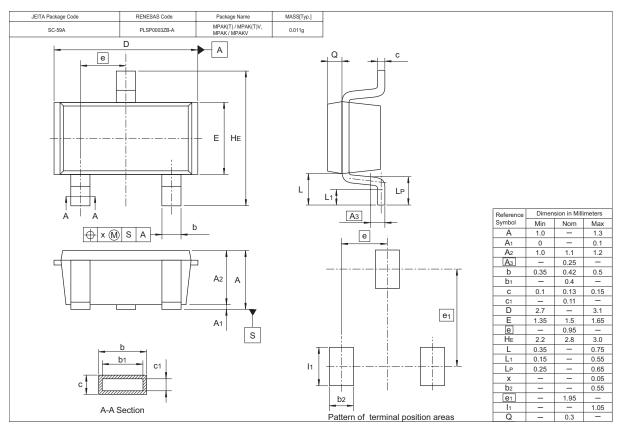


Main Characteristics





Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SA1121SCTL-E	3000	φ 178 mm Reel, 8 mm Emboss Taping
2SA1121SDTL-E		

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



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